

# PolarHV™ HiPerFET Power MOSFET

IXFA 14N60P  
IXFH 14N60P  
IXFP 14N60P

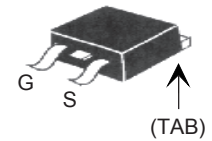
$V_{DSS} = 600 \text{ V}$   
 $I_{D25} = 14 \text{ A}$   
 $R_{DS(on)} \leq 550 \text{ m}\Omega$

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode

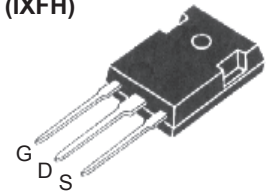


Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
$V_{DGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 1 \text{ M}\Omega$	600	V
$V_{GS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	14	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	42	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	14	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	23	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	0.9	J
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 4 \Omega$	10	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	300	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic body for 10 s	260	$^\circ\text{C}$
$M_d$	Mounting torque (TO-3P, TO-220)	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-220	4	g
	TO-263	2	g

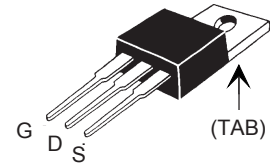
TO-263 (IXFA)



TO-247 (IXFH)



TO-220 (IXFP)



G = Gate  
S = Source

D = Drain  
TAB = Drain

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4 \text{ mA}$	3.5		5.5 V
$I_{GSS}$	$V_{GS} = \pm 30 \text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 100 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			5 $\mu\text{A}$
				50 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $d \leq 2\%$	450	550	$\text{m}\Omega$

## Features

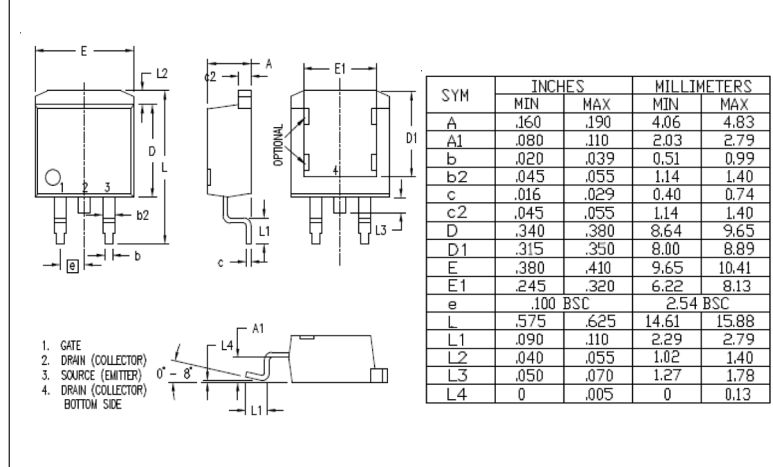
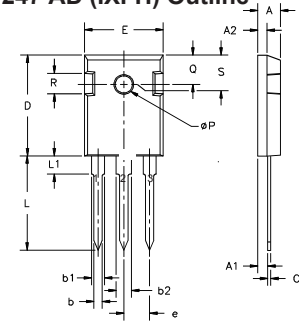
- † International standard packages
- † Unclamped Inductive Switching (UIS) rated
- † Low package inductance
- easy to drive and to protect

## Advantages

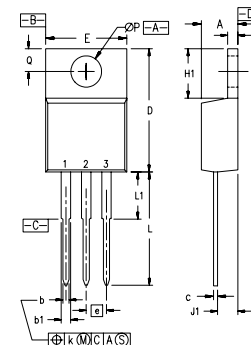
- † Easy to mount
- † Space savings
- † High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{ V}; I_D = 0.5 I_{D25}$ , pulse test	7	13	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	2300		pF
$C_{oss}$		215		pF
$C_{rss}$		13		pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = I_{D25}$ $R_G = 10\ \Omega$ (External)	23		ns
$t_r$		27		ns
$t_{d(off)}$		70		ns
$t_f$		26		ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$	38		nC
$Q_{gs}$		14		nC
$Q_{gd}$		12		nC
$R_{thJC}$ $R_{thCs}$	(TO-220)	0.25		$0.42^\circ\text{C/W}$ $^\circ\text{C/W}$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{ V}$			14 A
$I_{SM}$	Repetitive			42 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = 14\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$		6	200 ns
$I_{RM}$	$V_R = 100\text{ V}$			A
$Q_{RM}$			0.6	$\mu\text{C}$

**TO-263 (IXFA) Outline**

**TO-247 AD (IXFH) Outline**

 Terminals: 1 - Gate  
2 - Drain  
3 - Source  
Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L <sub>1</sub>	4.50		.177	
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

**TO-220 (IXFP) Outline**


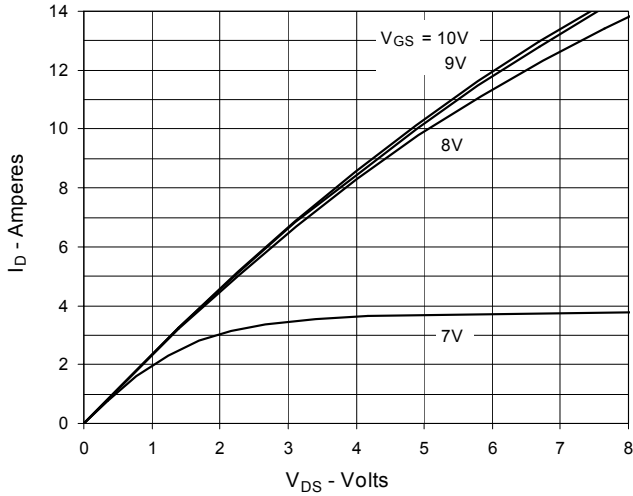
Pins: 1 - Gate 2 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
∅P	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

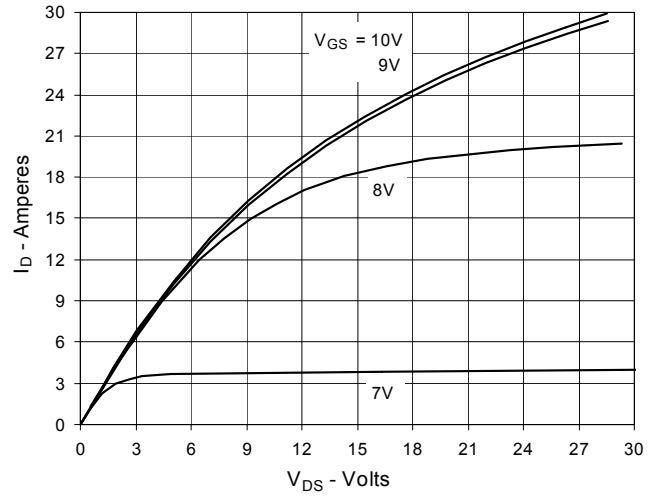
IXYS reserves the right to change limits, test conditions, and dimensions.

 IXYS MOSFETs and IGBTs are covered by 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585  
 one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692  
 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2

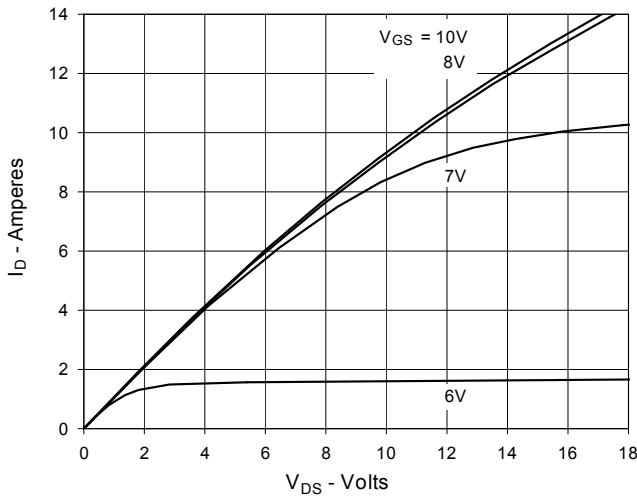
**Fig. 1. Output Characteristics @ 25°C**



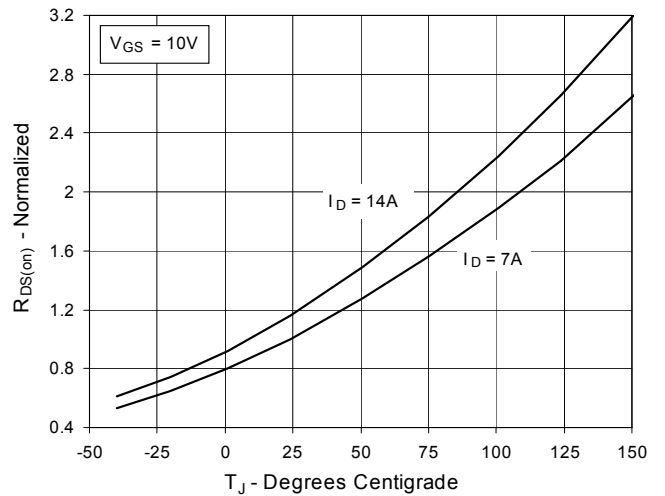
**Fig. 2. Extended Output Characteristics @ 25°C**



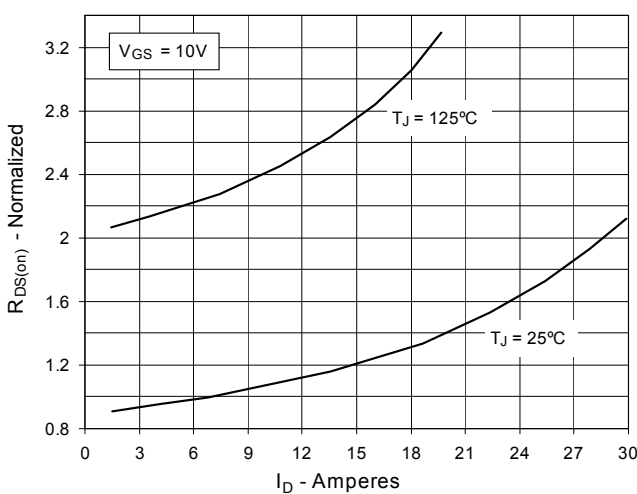
**Fig. 3. Output Characteristics @ 125°C**



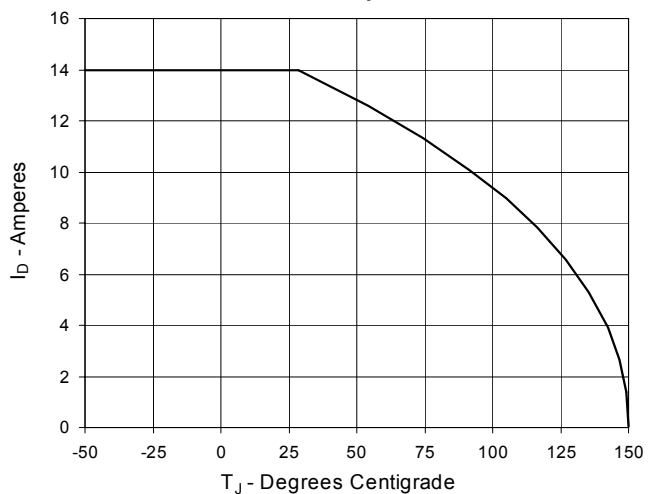
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 7A$  Value vs. Junction Temperature**



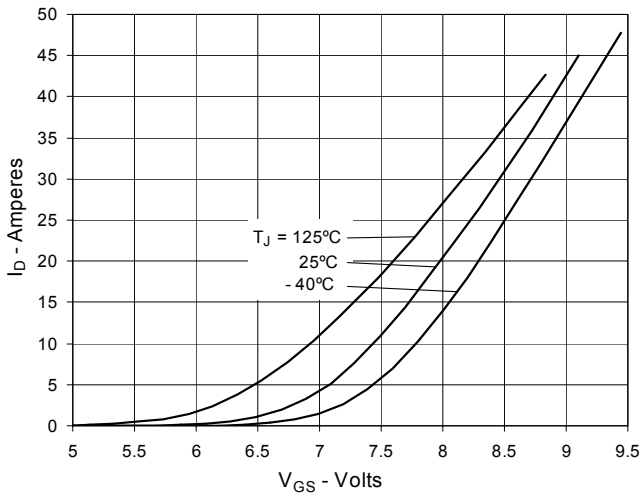
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 7A$  Value vs. Drain Current**



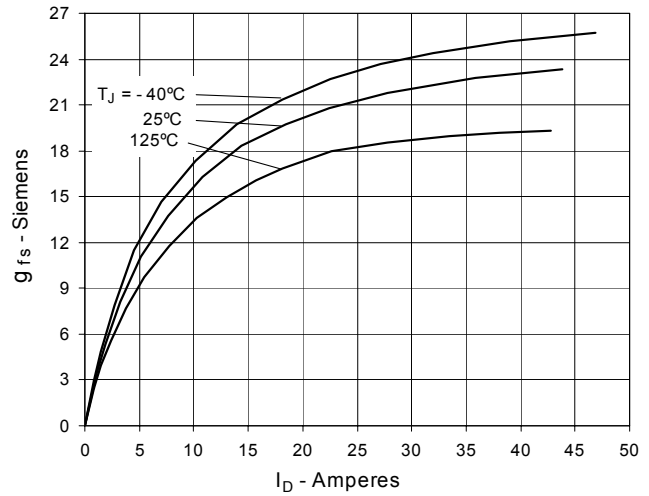
**Fig. 6. Maximum Drain Current vs. Case Temperature**



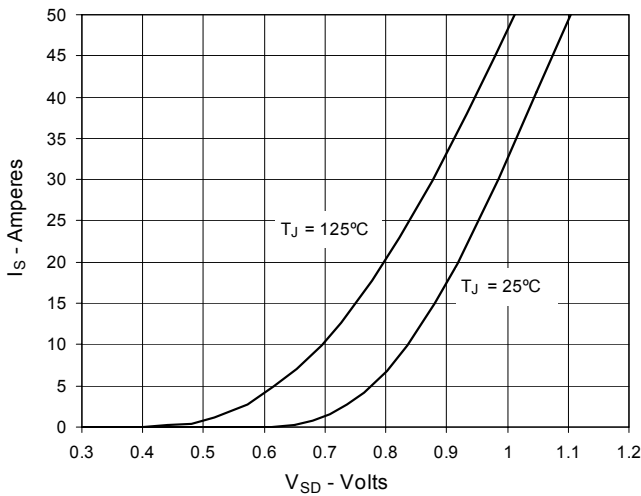
**Fig. 7. Input Admittance**



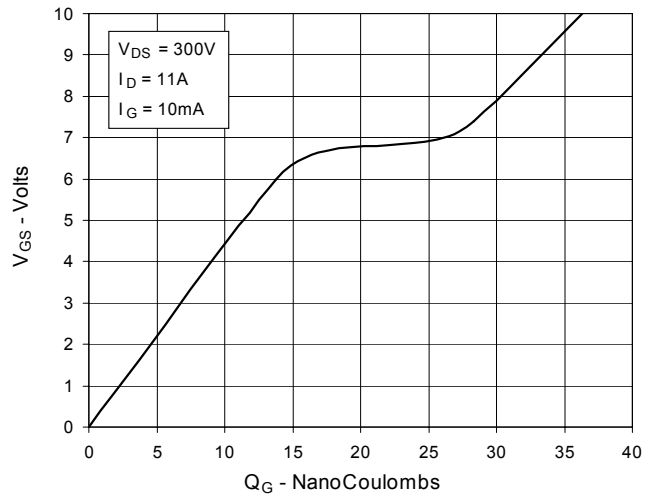
**Fig. 8. Transconductance**



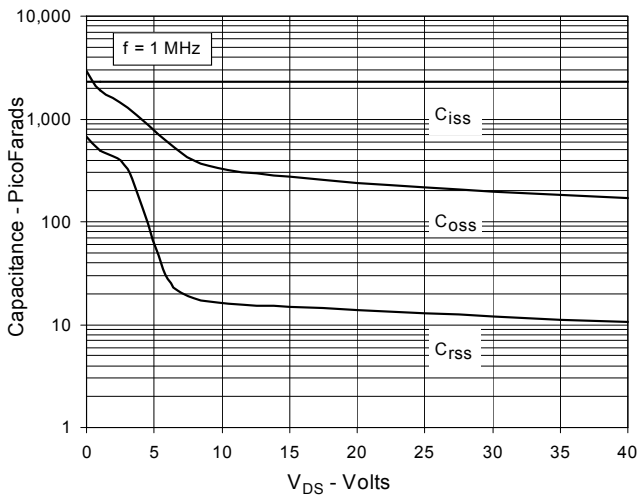
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**

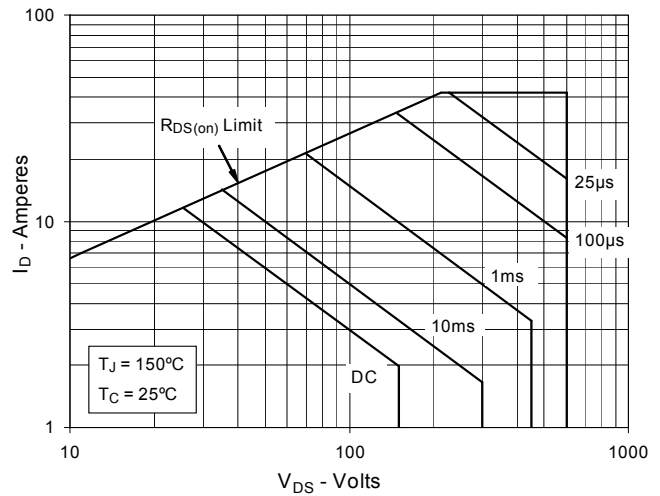


Fig. 13. Maximum Transient Thermal Resistance

